

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 2000-232153
(43)Date of publication of application : 22.08.2000

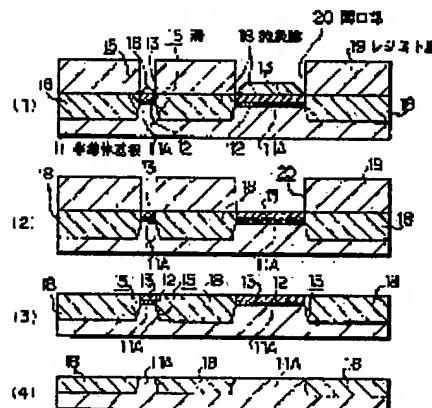
(51)Int.Cl.

H01L 21/76

(21)Application number : 11-032251
(22)Date of filing : 10.02.1999

(71)Applicant : SONY CORP
(72)Inventor : YAMAZAKI TAKESHI

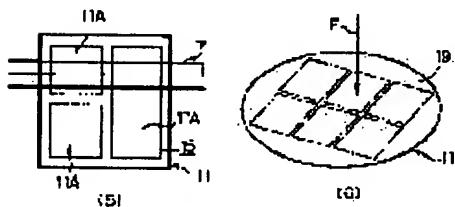
(54) MANUFACTURE OF SEMICONDUCTOR DEVICE



(57)Abstract:

PROBLEM TO BE SOLVED: To provide a technique by which an STI can be formed without performing CMP(chemical mechanical polishing) which raises a dishing problem nor requiring any active dummy pattern.

SOLUTION: A semiconductor device manufacturing method in which an element isolating area is formed by forming active area isolating grooves 15 into a semiconductor substrate 11 and filling up the grooves 15 with insulating films 18 includes a step of forming a resist film 19 on the insulating films 18 on the semiconductor substrate 11 so that the films may fill up the grooves 15, a step of generating data about the positions of patterns in an active area isolated by the element isolating area by directly reading the positions, and a step of forming an opening 20 through the resist film 19 on the active area by exposing and developing the film 19, based on the data. The method also includes a step of selectively removing the insulating films 18 on the active area from the opening 20.



LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]